

General Description

SFGMOS[®]

$R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The low V_{th} series is specially designed to use in synchronous rectification power systems with low driving voltage.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery



Applications

- PD charger
- Motor driver
- Switching voltage regulator
- DC-DC convertor
- Switched mode power supply

Key Performance Parameters

Parameter	Value	Unit
$V_{DS, min} @ T_{j(max)}$	100	V
$I_D, pulse$	45	A
$R_{DS(ON) max} @ V_{GS}=10V$	75	
Q_g	6.5	nC

Marking Information

Product Name	Package	Marking
SFG10R75DF	TO252	SFG10R75D

Package & Pin information



Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ unless otherwise noted

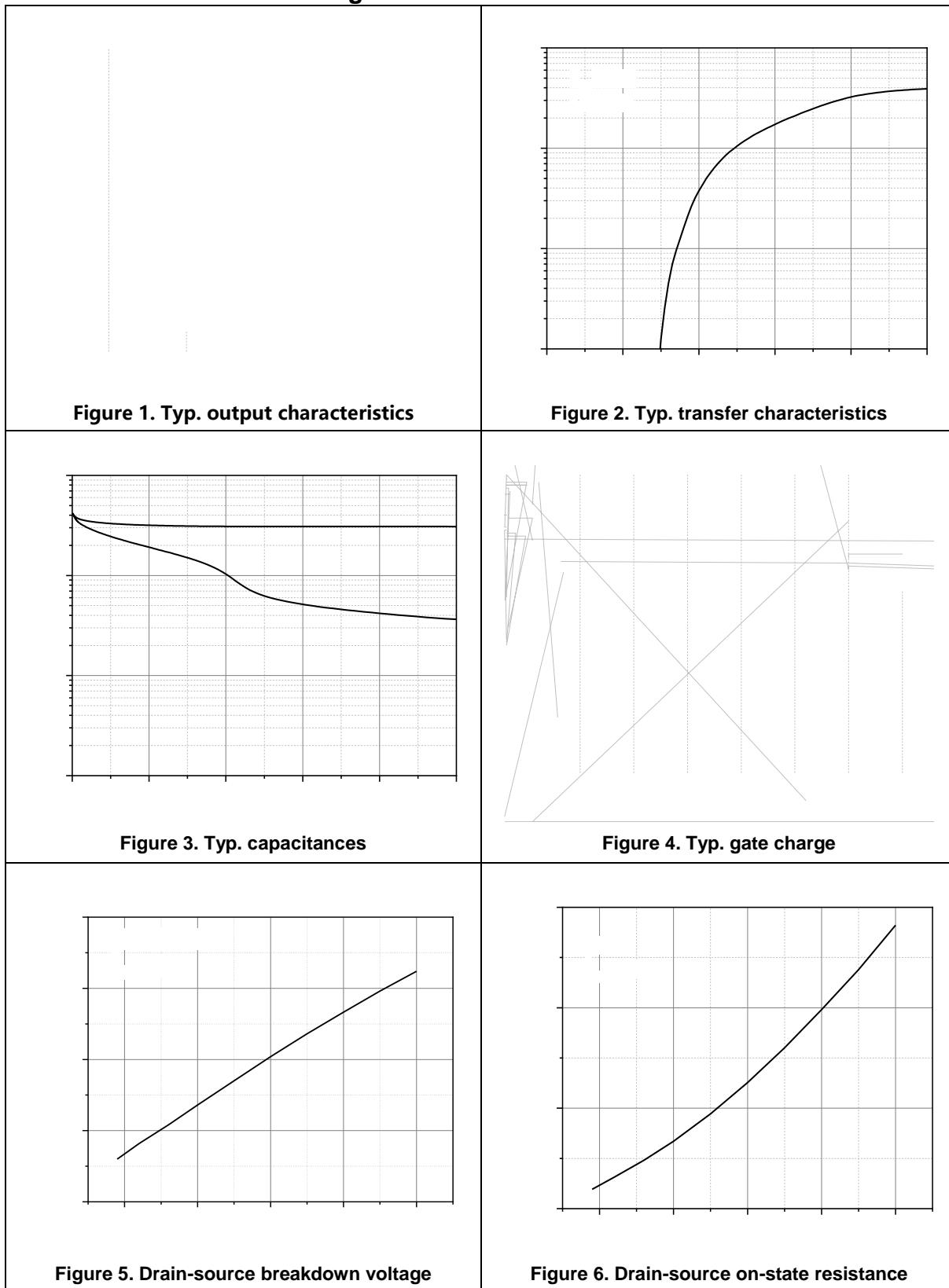
Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	100	V
Gate source voltage	V_{GS}	± 20	V
Continuous drain current ¹⁾ , $T_C=25\text{ }^\circ\text{C}$	I_D	15	A
Pulsed drain current ²⁾ , $T_C=25\text{ }^\circ\text{C}$	$I_{D,\text{pulse}}$	45	A

 Continuous diode forward current¹⁾, $T_C=25\text{ }^\circ\text{C}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		310		pF	$V_{GS}=0\text{ V},$ $V_{DS}=25\text{ V},$ 0 / kHz
Output capacitance	C_{oss}		171		pF	
Reverse transfer capacitance	C_{rss}		16.7		pF	
Turn-on delay time	$t_{d(on)}$		14		ns	$V_{GS}=10\text{ V},$ $V_{DS}=50\text{ V},$ $R_G=1\text{ }\Omega$ $I_D=5\text{ A}$
Rise time	t_r		3.2		ns	
Turn-off delay time	$t_{d(off)}$		36		ns	
Fall time	t_f					

Electrical Characteristics Diagrams



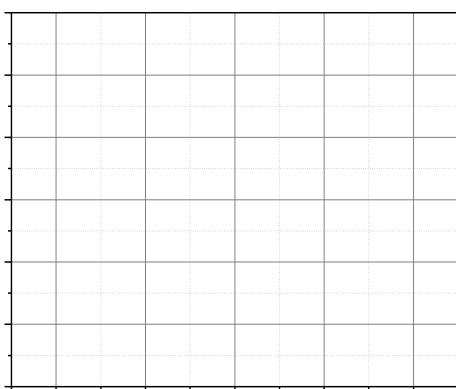


Figure 7. Threshold voltage

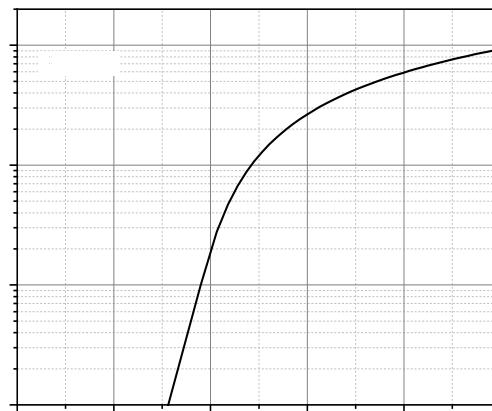


Figure 8. Forward characteristic of body diode

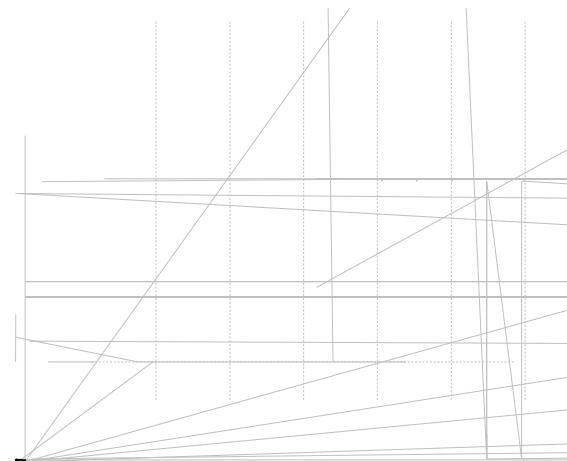


Figure 9. Drain-source on-state resistance

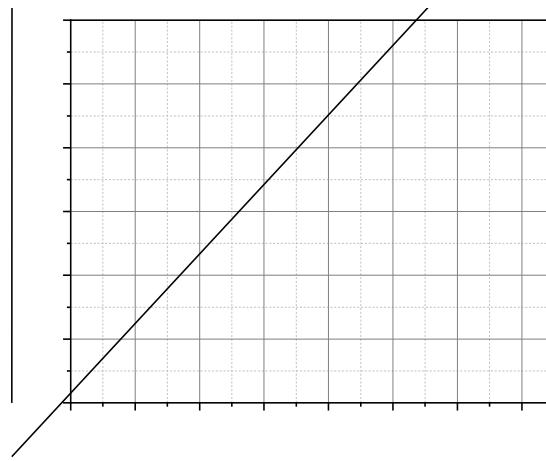


Figure 10. Drain current

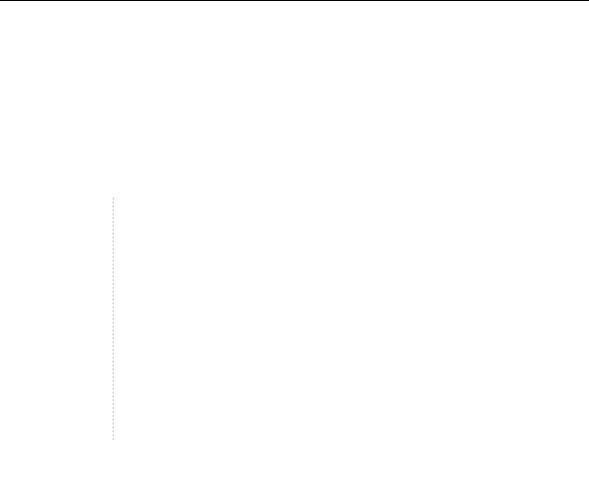


Figure 11. Safe operation area $T_c=25\text{ }^\circ\text{C}$

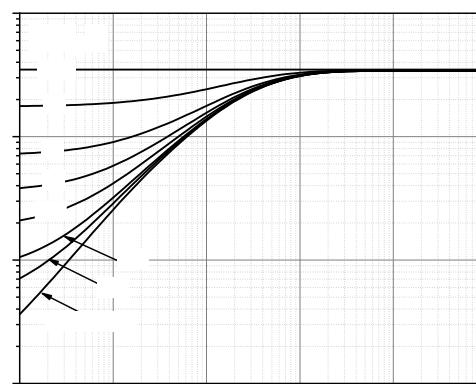


Figure 12. Max. transient thermal impedance

Test circuits and waveforms

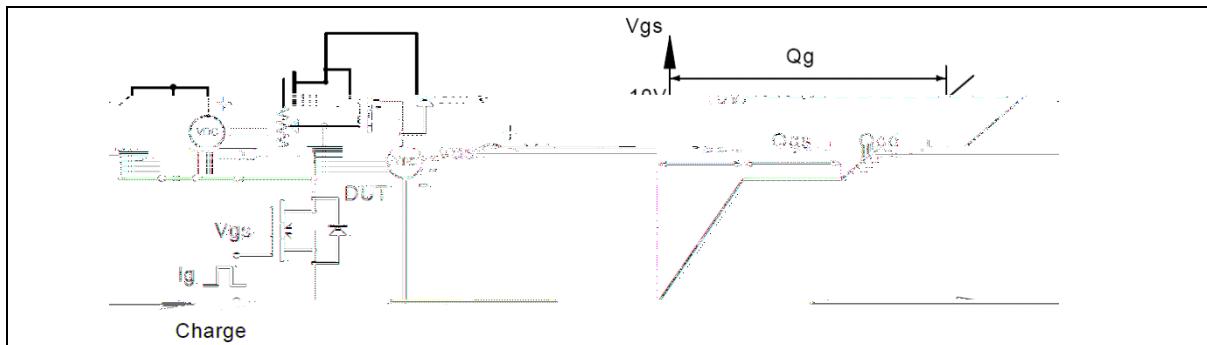


Figure 1. Gate charge test circuit & waveform

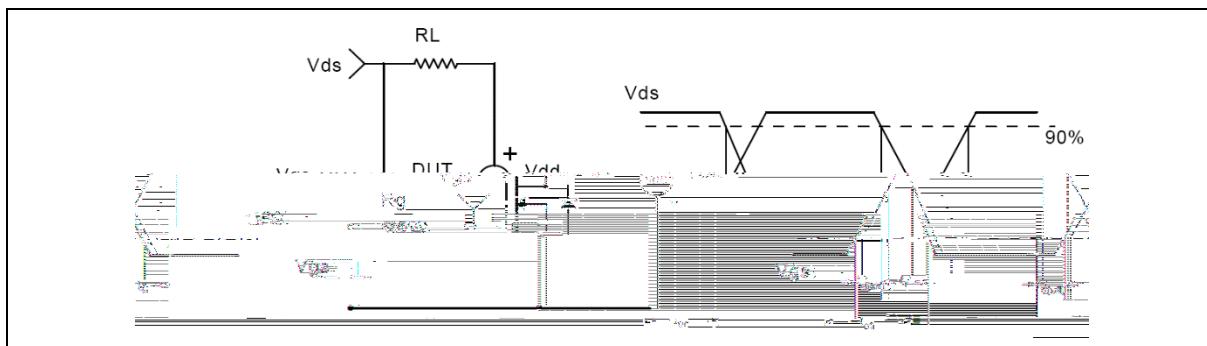


Figure 2. Switching time test circuit & waveform

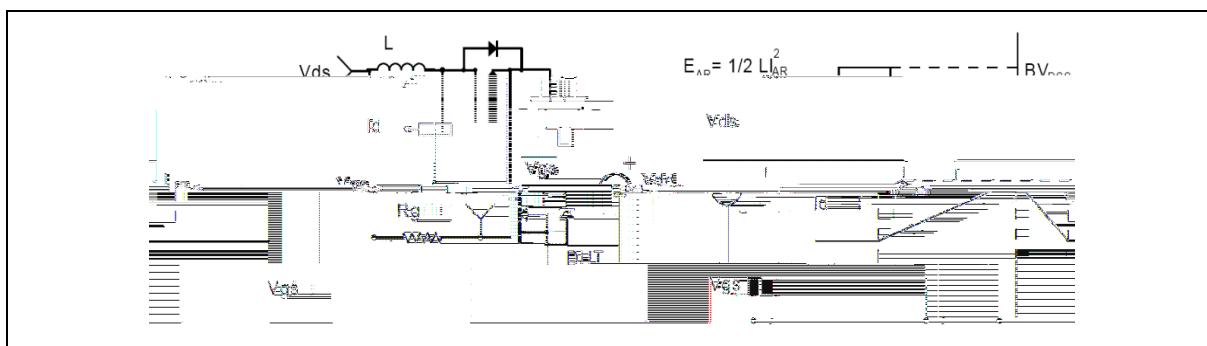


Figure 3. Unclamped inductive switching (UIS) test circuit & waveform

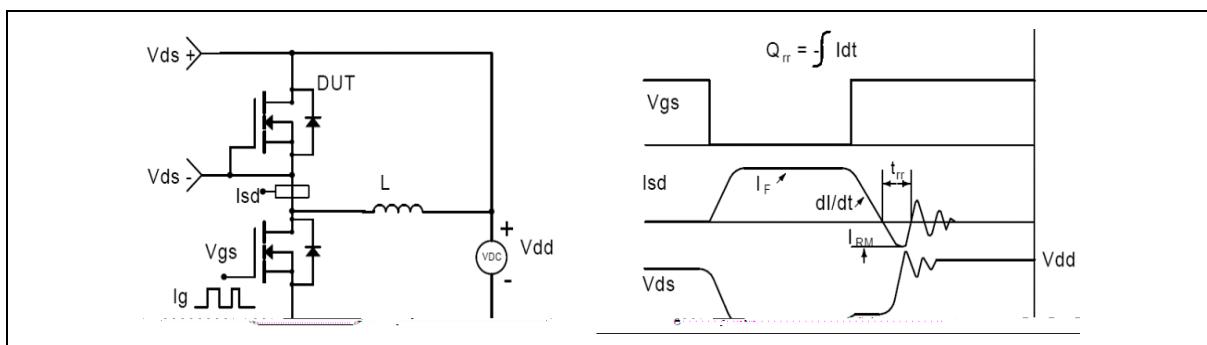
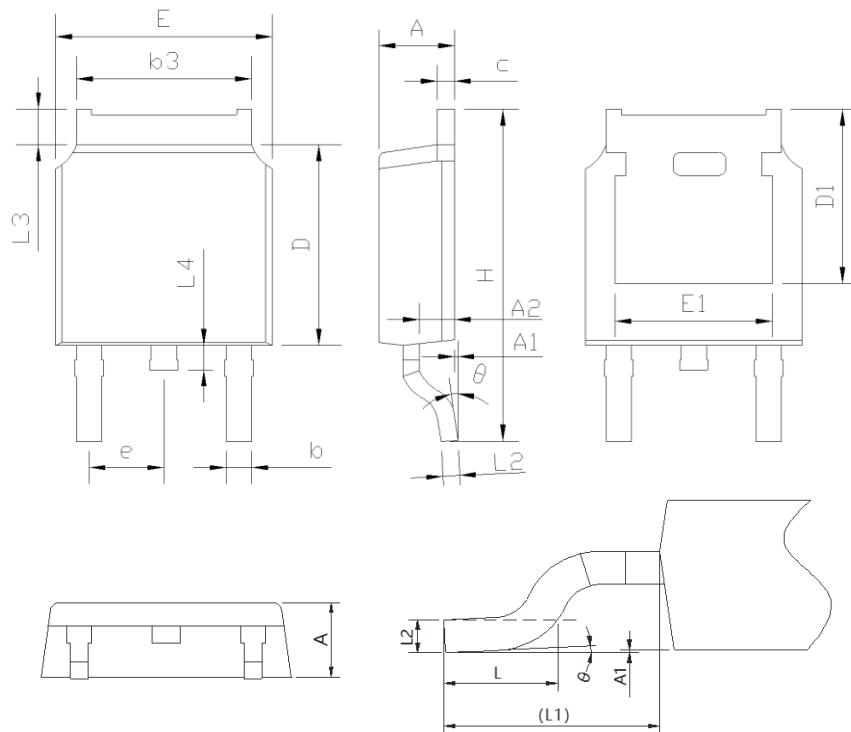


Figure 4. Diode reverse recovery test circuit & waveform

Package Information



Symbol	mm		
	Min	Nom	Max
A	2.20	2.30	2.38
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30 REF		
E	6.40	6.60	6.73
E1	4.63	-	-
e	2.286 BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90 REF		
L2	0.51 BSC		
L3	0.88	-	1.28
L4	0.50	-	1.00
	0	-	

Version 1: TO252-P package outline dimension

Package Information

Symbol	mm		
	Min	Nom	Max
A	2.20	2.30	2.38
A1	0.00	-	0.10
A2	0.90	1.01	1.10
b	0.72	-	0.85
b1	0.71	0.76	0.81
b2	0.72	-	0.90
b3	5.13	5.33	5.46
c	0.47	-	0.60
c1	0.46	0.51	0.56
c2	0.47	-	0.60
D	6.00	6.10	6.20
D1	5.25	-	-
E	6.50	6.60	6.70
E1	4.70	-	-
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1		2.90	

Ordering Information

Package Type	Units/Reel	Reels / Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO252-P	2500	2	5000	5	25000
TO252-J	2500	2	5000	5	25000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFG10R75DF	TO252	yes	yes	yes

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